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FCH35N60

N-Channel SuperFET® MOSFET

600 V, 35 A, 98 mΩ



Features

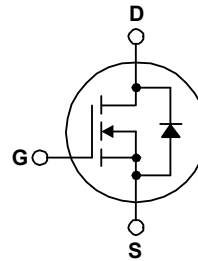
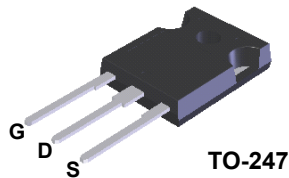
- 650 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 79\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 139\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 340\text{ pF}$)
- 100% Avalanche Tested

Application

- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCH35N60	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate-Source voltage	± 30	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	35
		- Continuous ($T_C = 100^\circ\text{C}$)	22.2
I_{DM}	Drain Current	- Pulsed (Note 1)	105
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	1455
I_{AR}	Avalanche Current	(Note 1)	35
E_{AR}	Repetitive Avalanche Energy	(Note 1)	31.25
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	20
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	312.5
		- Derate above 25°C	2.5
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCH35N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	42	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCH35N60	FCH35N60	TO-247	-	-	30

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V, T _J = 25°C	600	-	-	V
		I _D = 250 μA, V _{GS} = 0 V, T _J = 150°C	-	650	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	V _{GS} = 0 V, I _D = 16 A	-	700	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 480 V, T _C = 125°C	-	-	10	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 17.5 A	-	0.079	0.098	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 17.5 A	-	28.8	-	S

Dynamic Characteristics

C _{iSS}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V f = 1 MHz	-	4990	6640	pF
C _{oss}	Output Capacitance		-	2380	3170	pF
C _{rSS}	Reverse Transfer Capacitance		-	140	-	pF
C _{oss}	Output Capacitance	V _{DS} = 480 V, V _{GS} = 0 V, f = 1.0 MHz	-	113	-	pF
C _{oss eff.}	Effective Output Capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V	-	340	-	pF
Q _g	Total Gate Charge at 10V	V _{DS} = 480 V, I _D = 35 A V _{GS} = 10 V (Note 4)	-	139	181	nC
Q _{gs}	Gate to Source Gate Charge		-	31	-	nC
Q _{gd}	Gate to Drain "Miller" Charge		-	69	-	nC
ESR	Equivalent Series Resistance (G-S)	Drain Open, F = 1 MHz	-	1.4	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 35 A R _G = 4.7 Ω (Note 4)	-	34	78	ns
t _r	Turn-On Rise Time		-	120	250	ns
t _{d(off)}	Turn-Off Delay Time		-	105	220	ns
t _f	Turn-Off Fall Time		-	73	155	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	35	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	105	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 35 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 35 A	-	614	-	ns
Q _{rr}	Reverse Recovery Charge	di _F /dt = 100 A/μs	-	16.3	-	μC

Notes:

- 1: Repetitive Rating; Pulse-width limited by maximum junction temperature.
- 2: I_{AS} = 17.5 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C
- 3: I_{SD} ≤ 35 A, di_F/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C
- 4: Essentially independent of operating temperature.

Typical Characteristics

Figure 1. On-Region Characteristics

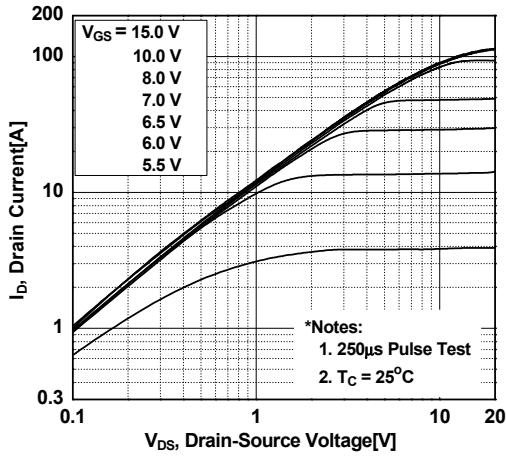


Figure 2. Transfer Characteristics

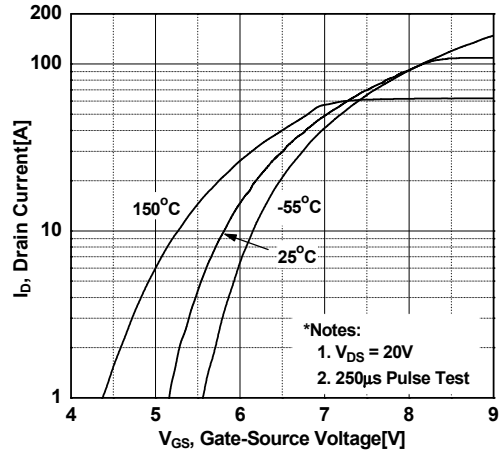


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

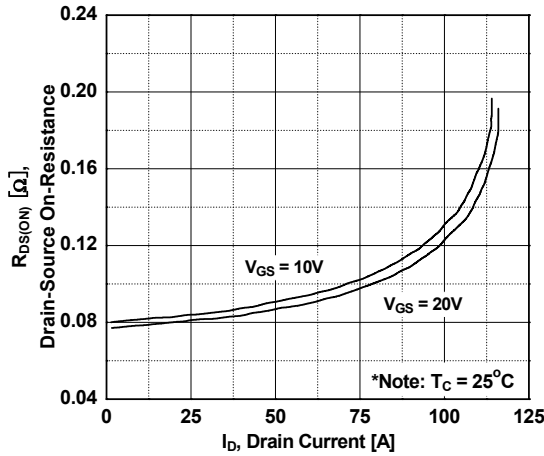


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

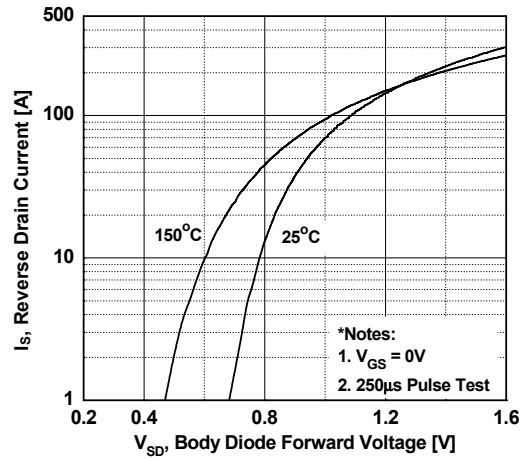


Figure 5. Capacitance Characteristics

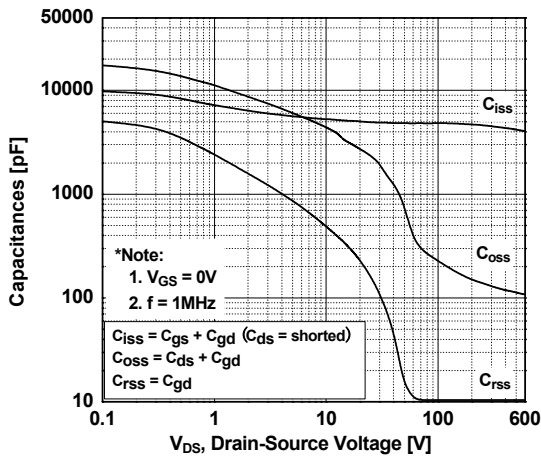
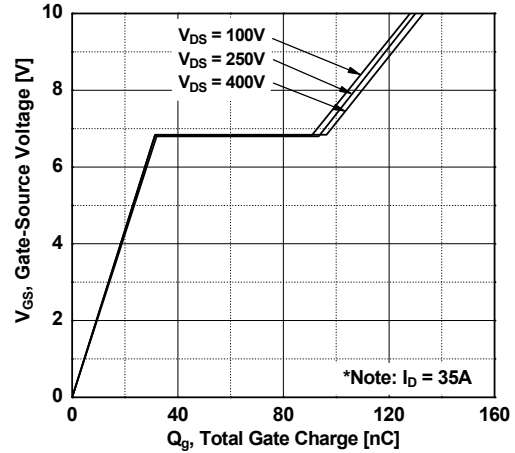


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

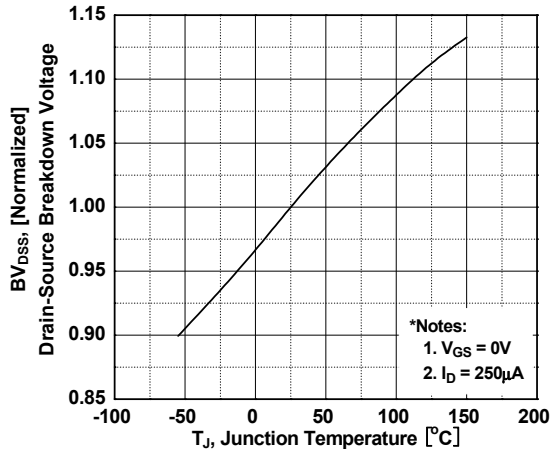


Figure 8. On-Resistance Variation vs. Temperature

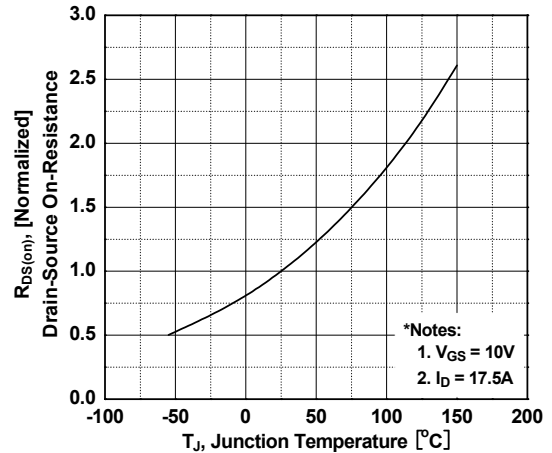


Figure 9. Maximum Safe Operating Area

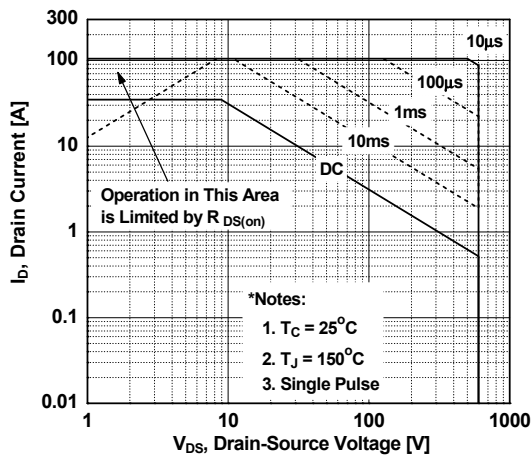


Figure 10. Maximum Drain Current vs. Case Temperature

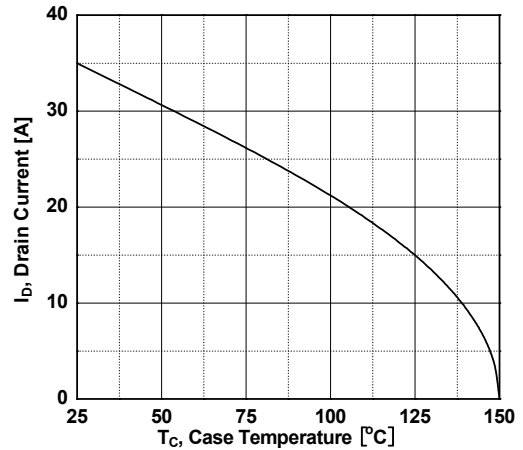


Figure 11. Transient Thermal Response Curve

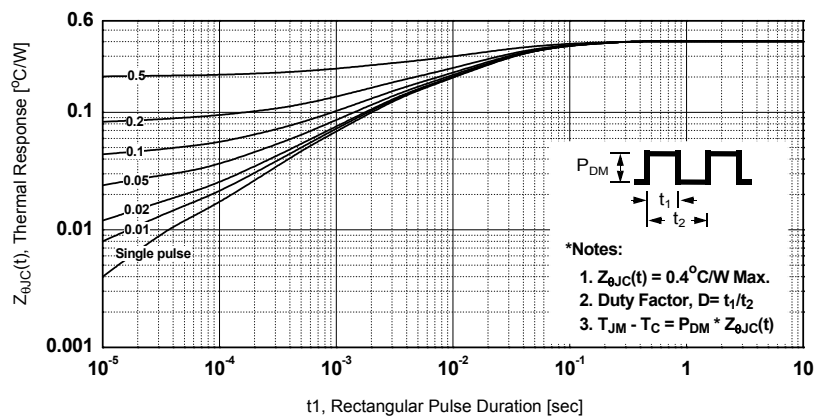


Figure 12. Gate Charge Test Circuit & Waveform

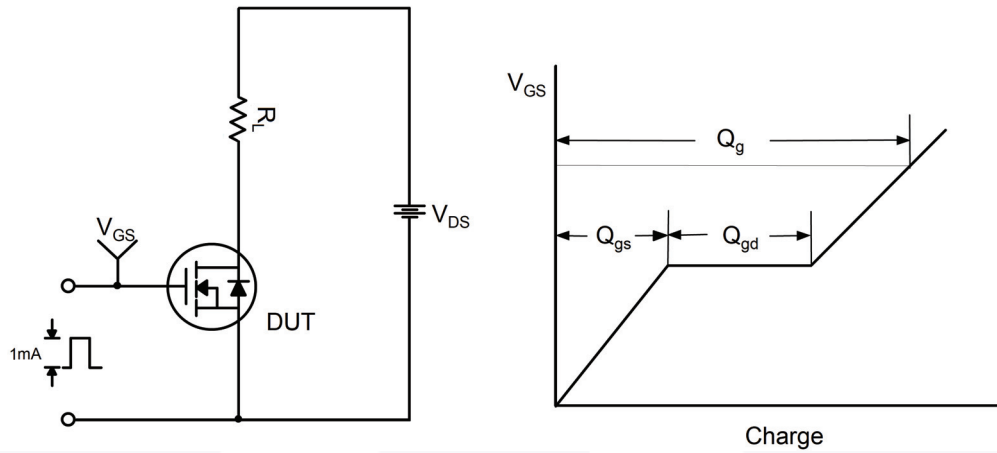


Figure 13. Resistive Switching Test Circuit & Waveforms

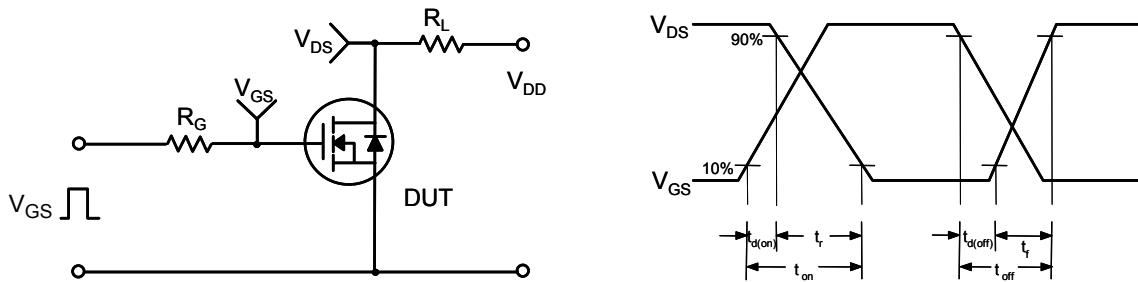


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

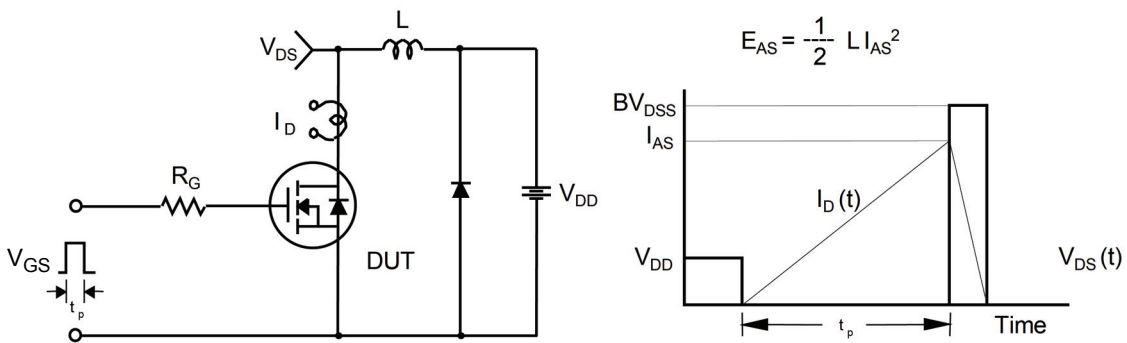
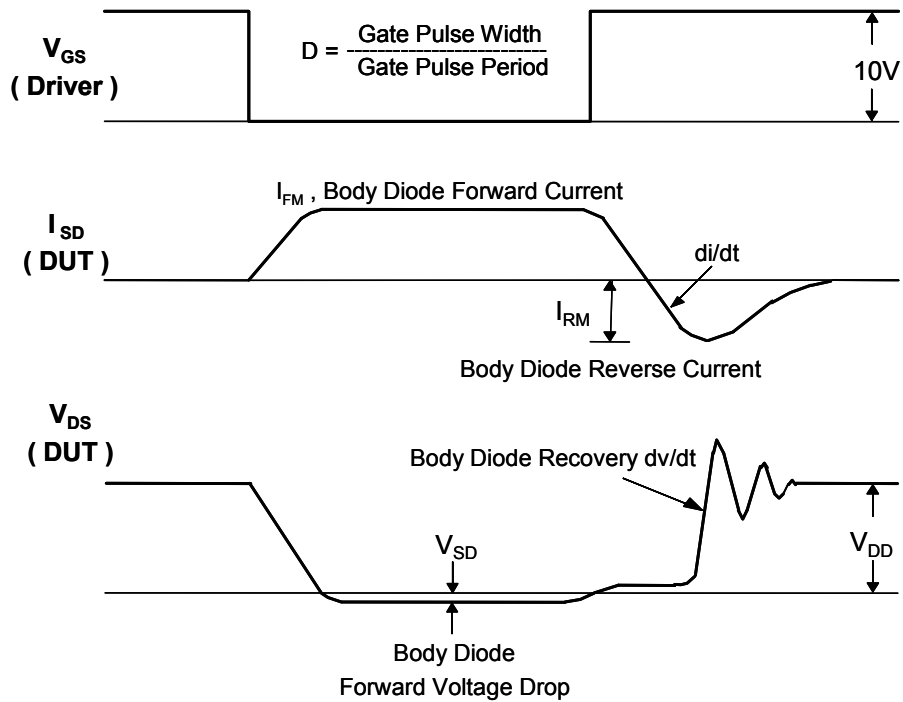
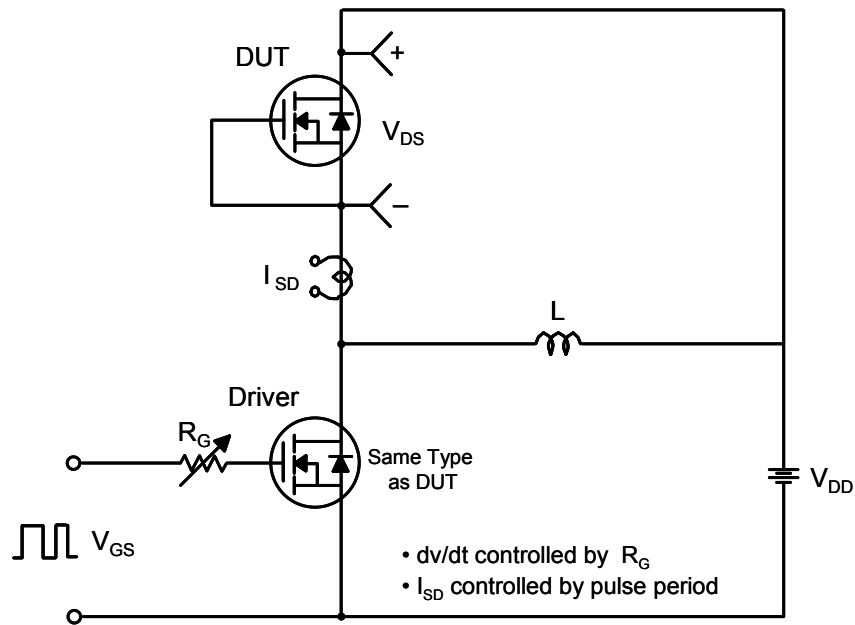
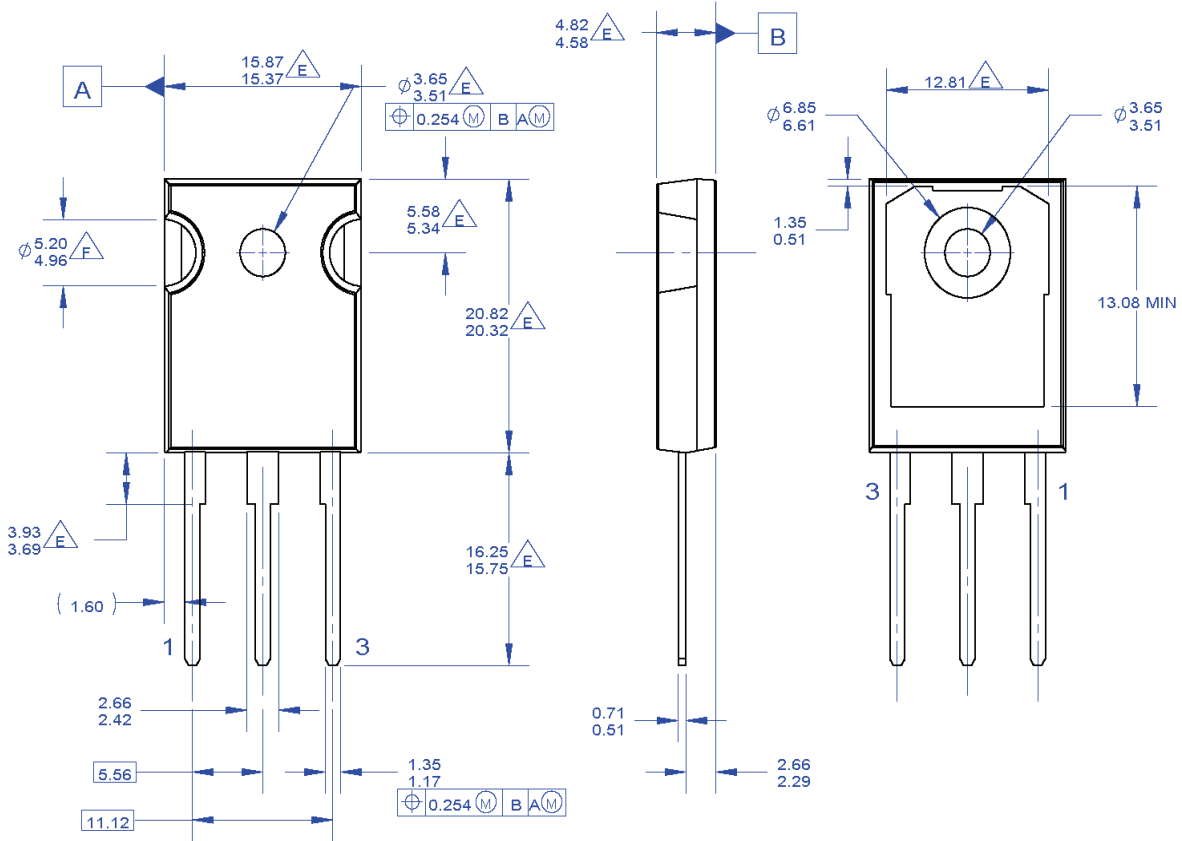


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-247 3L



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Figure ... TO-247, Molded, 3 Lead, Jedec Variation AB

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